



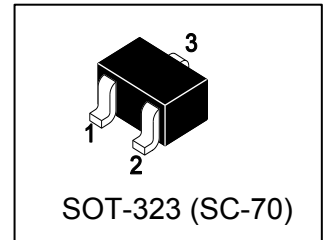
N-Channel Enhancement MOSFET



VDS= 50V, ID= 200mA

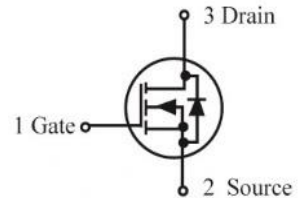
Features

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- Low threshold voltage (VGS(th): 0.5V...1.5V) makes it ideal for low voltage applications.



MARKING

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PACKAGE INFORMATION

Package	Shipping
SOT-323	3000/Tape&Reel

MAXIMUM RATINGS (TA = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	50	Vdc
Gate-to-Source Voltage – Continuous	V _{GS}	± 20	Vdc
Drain Current	I _D	200	mA
– Pulsed Drain Current (t _p ≤ 10 μs)	I _{DM}	800	
Total Power Dissipation @ TA = 25°C	P _D	150	mW
Operating and Storage Temperature Range	T _J , T _{stg}	– 55 to 150	°C
Thermal Resistance – Junction-to-Ambient	R _{θJA}	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T _L	260	°C

1. FR-5 = 1.0×0.75×0.062 in.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 250\ \mu\text{Adc}$)	$V_{(BR)DSS}$	50	–	–	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 25\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = 50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	– –	– –	0.1 0.5	μAdc
Gate-Source Leakage Current ($V_{GS} = \pm 20\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	–	–	± 0.1	μAdc

ON CHARACTERISTICS (Note 1.)

Gate-Source Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.0\text{ mAdc}$)	$V_{GS(th)}$	0.5	–	1.5	Vdc
Static Drain-to-Source On-Resistance ($V_{GS} = 2.75\text{ Vdc}$, $I_D < 200\text{ mAdc}$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$) ($V_{GS} = 5.0\text{ Vdc}$, $I_D = 200\text{ mAdc}$)	$r_{DS(on)}$	– –	5.6 –	10 3.5	Ohms
Forward Transconductance ($V_{DS} = 25\text{ Vdc}$, $I_D = 200\text{ mAdc}$, $f = 1.0\text{ kHz}$)	g_{fs}	100	–	–	mmhos

DYNAMIC CHARACTERISTICS

Input Capacitance	($V_{DS} = 25\text{ Vdc}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{iss}	–	40	50	pF
Output Capacitance	($V_{DS} = 25\text{ Vdc}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{oss}	–	12	25	
Transfer Capacitance	($V_{DG} = 25\text{ Vdc}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{rss}	–	3.5	5.0	

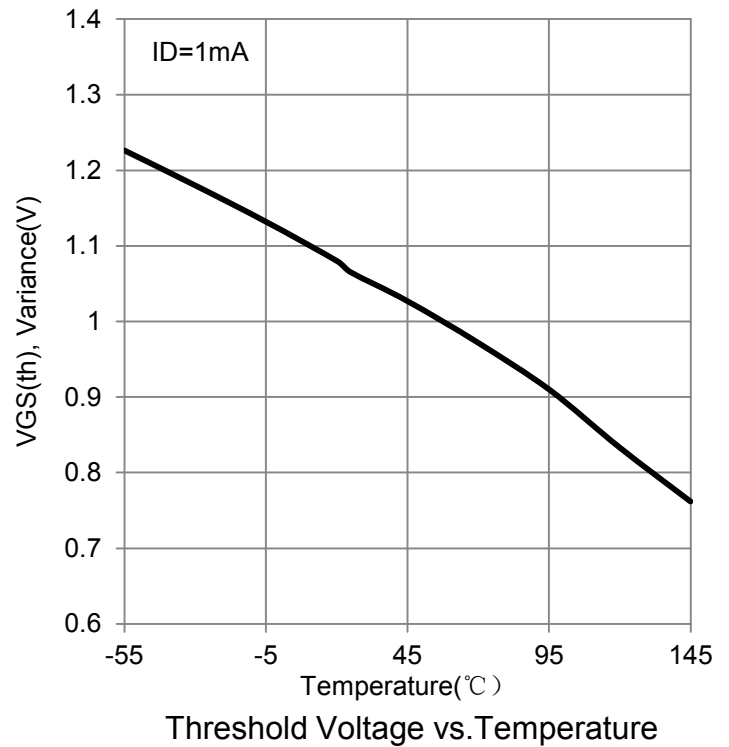
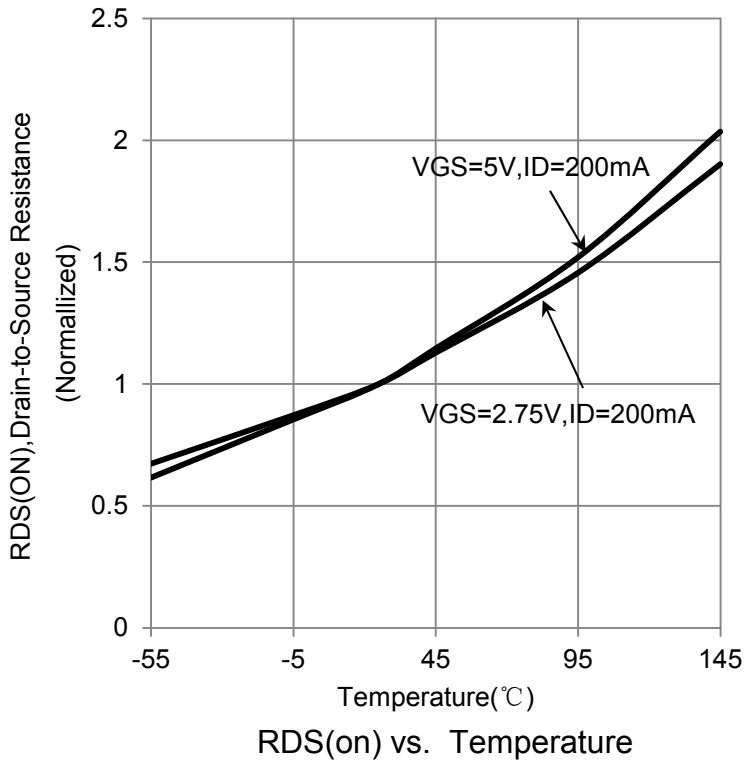
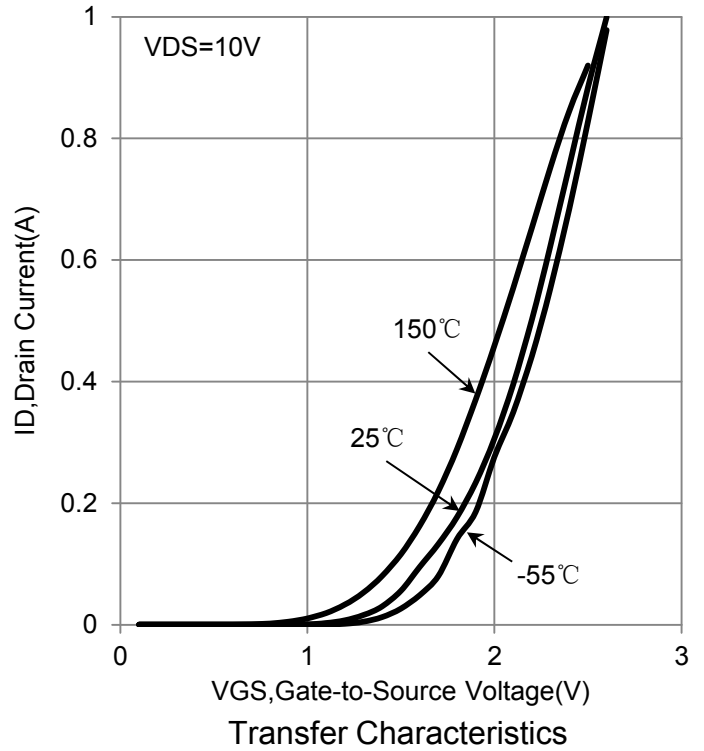
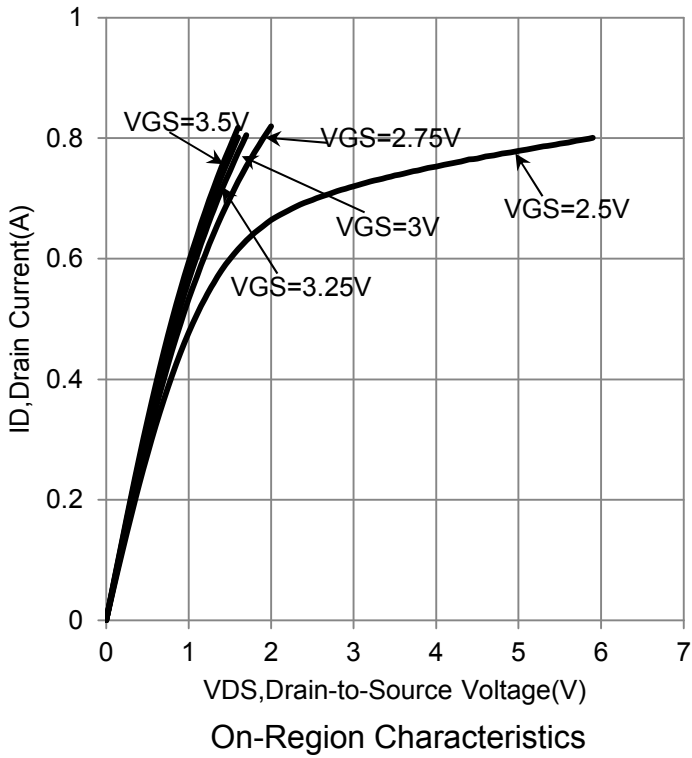
SWITCHING CHARACTERISTICS (Note 2.)

Turn-On Delay Time	($V_{DD} = 30\text{ Vdc}$, $I_D = 0.2\text{ Adc}$)	$t_{d(on)}$	–	–	20	ns
Turn-Off Delay Time		$t_{d(off)}$	–	–	20	

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.
2. Switching characteristics are independent of operating junction temperature.

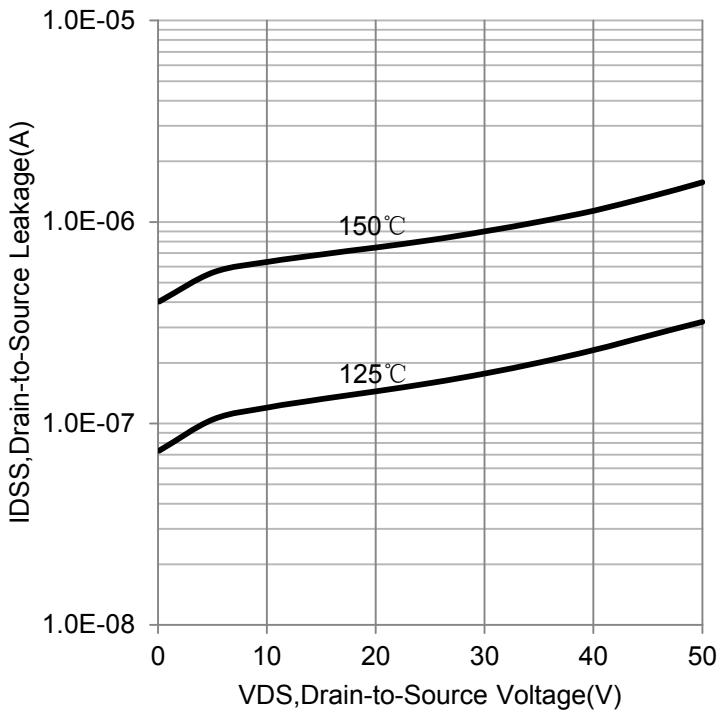
DEVICE CHARACTERISTICS

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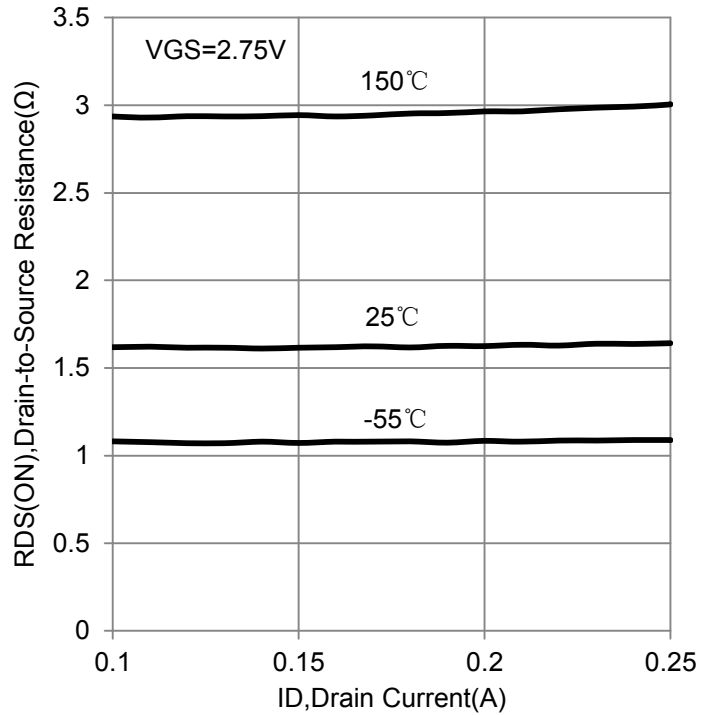


DEVICE CHARACTERISTICS

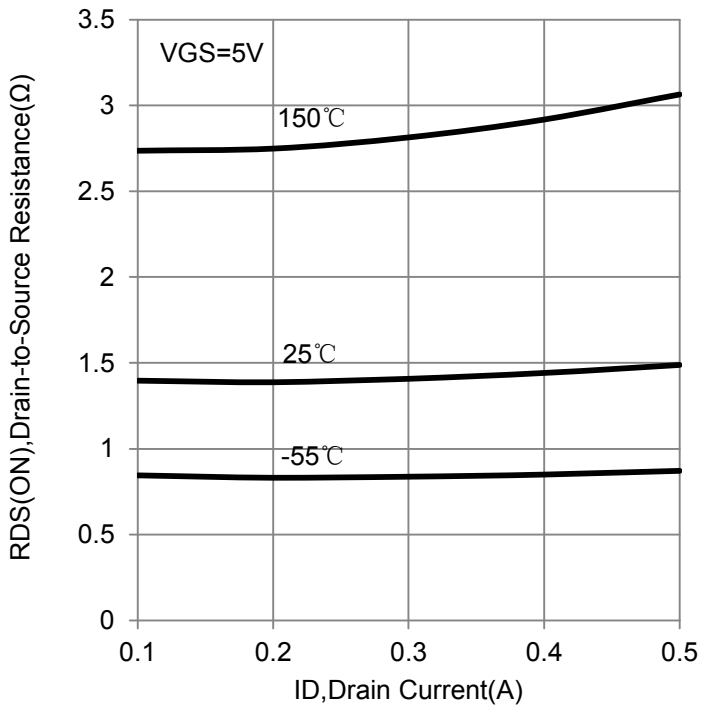
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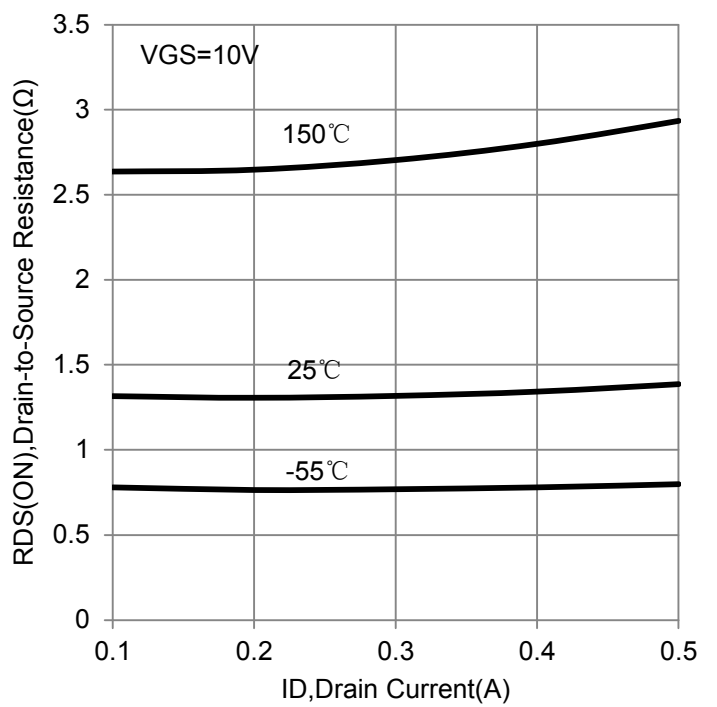
IDSS vs. VDS



RDS(on) vs. ID



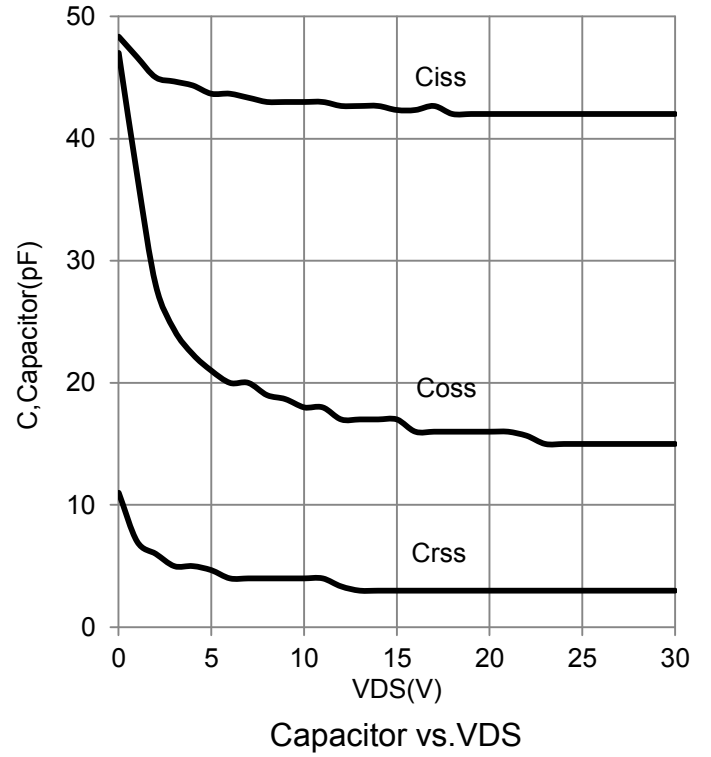
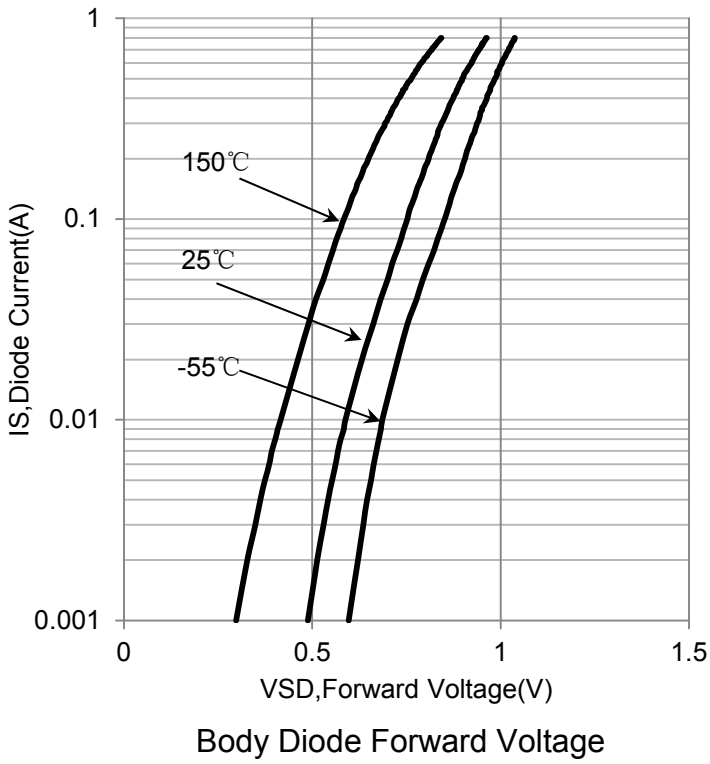
RDS(on) vs. ID



RDS(on) vs. ID

DEVICE CHARACTERISTICS

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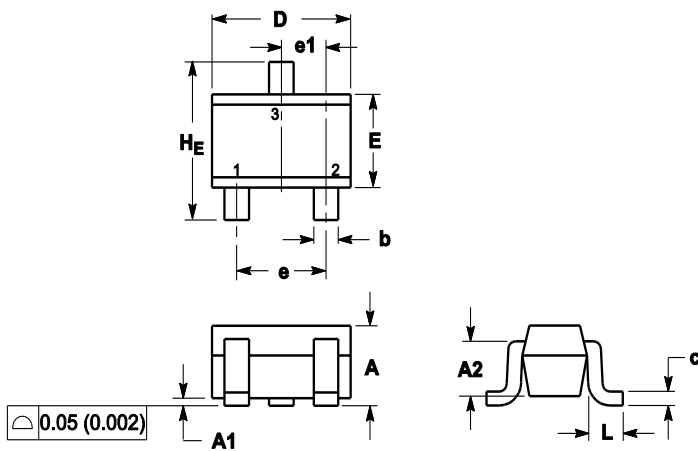
PACKAGE OUTLINE & DIMENSIONS

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OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70REF			0.028REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65REF			0.026REF		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

SOLDERING FOOTPRINT

